

BUK761R6-40E

N-channel TrenchMOS standard level FET 5 September 2013

Product data sheet

General description 1.

Standard level N-channel MOSFET in a SOT404A package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

Features and benefits 2.

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with V_{GS(th)} rating of greater than 1 V at 175 °C

Applications

- 12 V Automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	40	V	
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u>	[1]	-	-	120	Α	
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	349	W	
Static characte	Static characteristics							
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 11		-	1.3	1.57	mΩ	
Dynamic characteristics								
Q_{GD}	gate-drain charge	V _{GS} = 10 V; I _D = 25 A; V _{DS} = 32 V; Fig. 13; Fig. 14		-	48.2	-	nC	

[1] Continuous current is limited by package.



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D I
2	D	drain		
3	S	source		G (F) (A)
mb	D	mounting base; connected to drain	D2PAK (SOT404A)	mbb076 S

6. Ordering information

Table 3. Ordering information

Type number	Package						
	Name	Description	Version				
BUK761R6-40E	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404A				

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK761R6-40E	BUK761R6-40E

8. Limiting values

Table 5. Limiting values

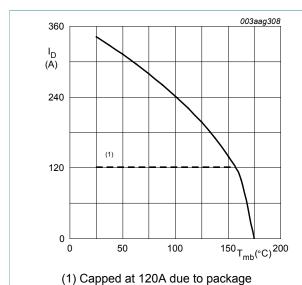
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	40	V
V_{DGR}	drain-gate voltage	R_{GS} = 20 k Ω		-	40	V
V_{GS}	gate-source voltage	T _j ≤ 175 °C; DC		-20	20	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u>	[1]	-	120	Α
		T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 1</u>	[1]	-	120	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; Fig. 4		-	1355	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	349	W
T _{stg}	storage temperature			-55	175	°C
T _j	junction temperature			-55	175	°C
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Symbol	Parameter	Conditions		Min	Max	Unit		
Source-drain	Source-drain diode							
Is	source current	T _{mb} = 25 °C	[1]	-	120	Α		
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	1355	Α		
Avalanche ruggedness								
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 120 A; $V_{sup} \le 40$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 3	[2][3]	-	1008	mJ		

- Continuous current is limited by package. Single-pulse avalanche rating limited by maximum junction temperature of 175 $^{\circ}\text{C}.$
- Refer to application note AN10273 for further information.



Continuous drain current as a function of Fig. 1.

mounting base temperature

$$V_{GS} \ge 10V$$

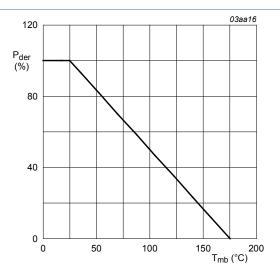


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

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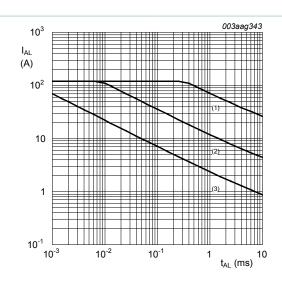
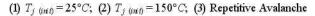


Fig. 3. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time



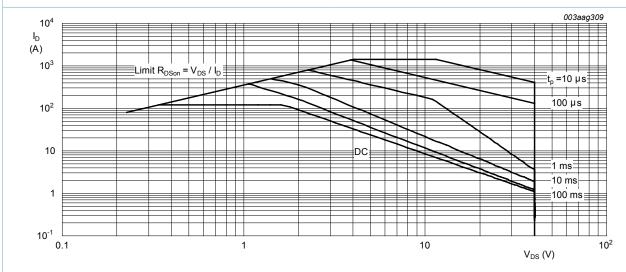


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb} = 25^{\circ}C$; I_{DM} is a single pulse

9. Thermal characteristics

Table 6. Thermal characteristics

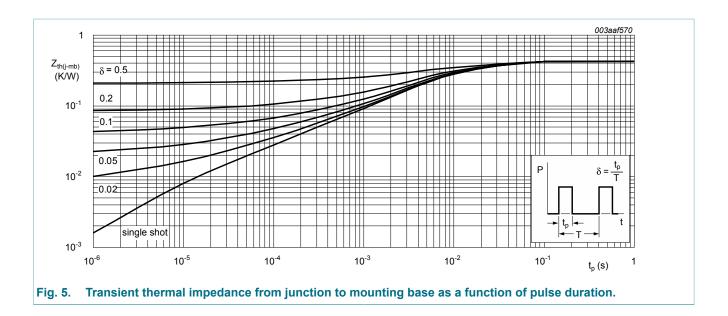
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	0.43	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint ; mounted on a printed-circuit board	-	50	-	K/W

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static charact	eristics						
V _{(BR)DSS}	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$		40	-	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C		36	-	-	V
V _{GS(th)}	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 9; Fig. 10		2.4	3	4	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C; Fig. 10		-	-	4.5	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 10		1	_	_	V
I _{DSS}	drain leakage current	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$		-	0.25	2	μA
		V _{DS} = 40 V; V _{GS} = 0 V; T _j = 175 °C		-	-	500	μA
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$		-	2	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C		-	2	100	nA
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 11		-	1.3	1.57	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 12; Fig. 11		-	-	3	mΩ
Dynamic characteristics							
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 32 V; V _{GS} = 10 V;		-	145	-	nC
Q _{GS}	gate-source charge	Fig. 13; Fig. 14		-	35.7	-	nC
Q_{GD}	gate-drain charge			-	48.2	-	nC

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; Fig. 15$		-	8500	11340	pF
C _{oss}	output capacitance			-	1620	1950	pF
C _{rss}	reverse transfer capacitance			-	985	1350	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V};$		-	42	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$		-	60	-	ns
t _{d(off)}	turn-off delay time			-	121	-	ns
t _f	fall time			-	83	-	ns
L _D	internal drain inductance	from upper edge of drain mounting base to center of die		-	2.5	-	nΗ
L _S	internal source inductance	from source lead to source bonding pad		-	7.5	-	nH
Source-dra	in diode						J
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 16$		-	0.77	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$		-	56	-	ns
Q _r	recovered charge	V _{DS} = 25 V		-	94	-	nC

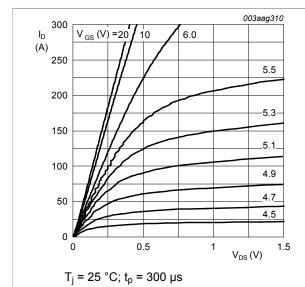


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

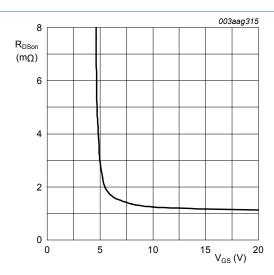


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25 \,^{\circ}C; I_D = 25A$$

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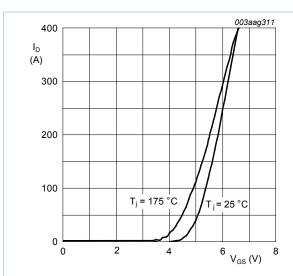


Fig. 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values



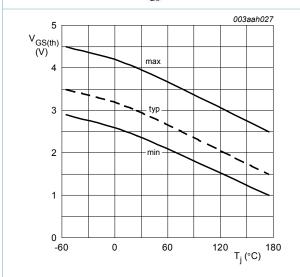


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 \text{ mA}; \ V_{DS} = V_{GS}$$

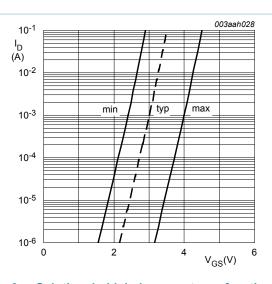
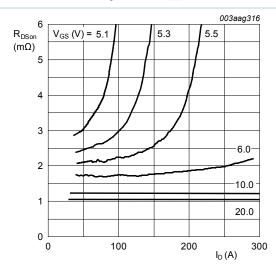


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25^{\circ}C; \ V_{DS} = 5V$$



 $T_i = 25 \,^{\circ}\text{C}; t_p = 300 \,\mu\text{s}$

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

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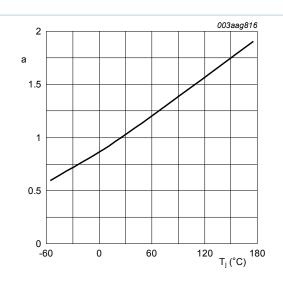


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$\mathbf{a} = \frac{R_{DSon}}{R_{DSon(25~\mathrm{C})}}$$

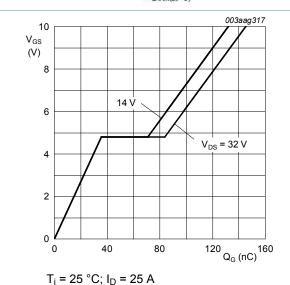


Fig. 14. Gate-source voltage as a function of gate charge; typical values

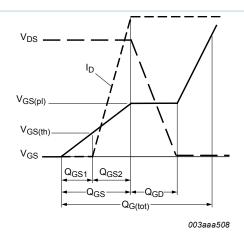


Fig. 13. Gate charge waveform definitions

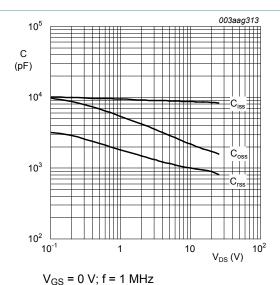
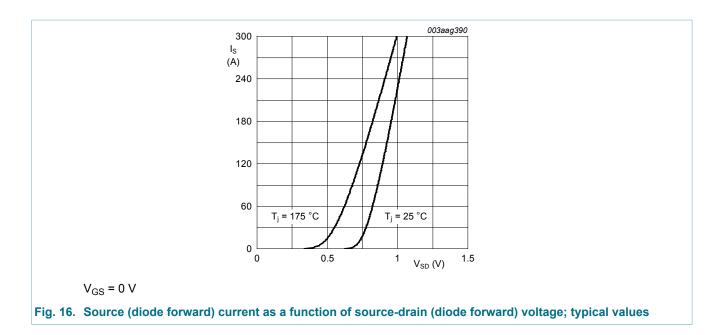


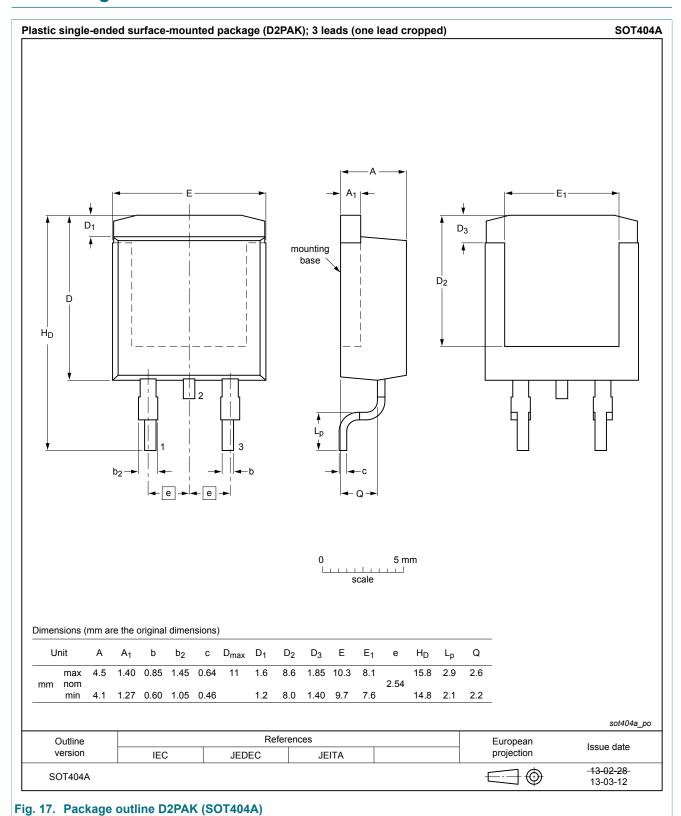
Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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11. Package outline



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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
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